# DATA SHEET

# MOS FIELD EFFECT TRANSISTOR μ **PA678TB**

# P-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

## DESCRIPTION

NEC

The  $\mu$  PA678TB is a switching device, which can be driven directly by a 2.5 V power source.

The  $\mu$  PA678TB features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

#### **FEATURES**

- 2.5 V drive available
- Low on-state resistance
- $R_{DS(on)1} = 1.45 \Omega MAX. (V_{GS} = -4.5 V, I_{D} = -0.20 A)$
- $R_{DS(on)2} = 1.55 \Omega MAX. (V_{GS} = -4.0 V, I_{D} = -0.20 A)$
- $R_{DS(on)3} = 2.98 \Omega MAX. (V_{GS} = -2.5 V, I_{D} = -0.15 A)$
- Two MOS FET circuits in same size package as SC-70

### ORDERING INFORMATION

PART NUMBER	PACKAGE
$\mu$ PA678TB	SC-88 (SSP)

#### Marking: XA

#### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ )

Drain to Source Voltage (Vgs = 0 V)	VDSS	-20	V
Gate to Source Voltage (VDS = 0 V)	Vgss	∓12	V
Drain Current (DC)	ID(DC)	∓0.25	А
Drain Current (pulse) <sup>Note1</sup>	D(pulse)	<b>∓1.00</b>	А
Total Power Dissipation (2 units) Note2	Ρτ	0.2	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	–55 to +150	°C

**Notes 1.** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%

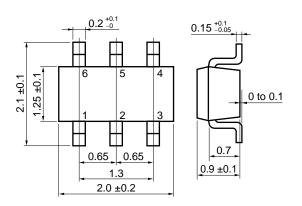
2. Mounted on FR-4 board of 2500 mm<sup>2</sup> x 1.1 mm

Caution This product is electrostatic-sensitive device due to low ESD capability and shoud be handled with caution for electrostatic discharge. VESD =  $\pm 100$  V TYP. (C = 200 pF, R = 0  $\Omega$ , Single pulse)

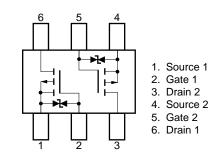
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## PACKAGE DRAWING (Unit: mm)



#### **PIN CONNECTION (Top View)**

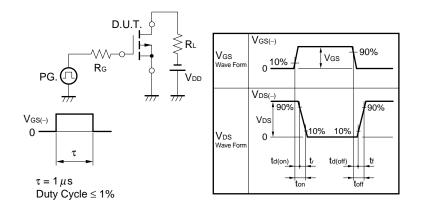


ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)

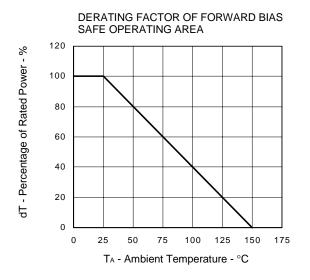
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	Idss	Vds = -20.0 V, Vgs = 0 V			-1.0	μA
Gate Leakage Current	lgss	Vgs = ∓12.0 V, Vds = 0 V			∓10	μA
Gate Cut-off Voltage Note	V <sub>GS(off)</sub>	V <sub>DS</sub> = -10.0 V, I <sub>D</sub> = -1.0 mA	-0.8	-1.3	-1.8	V
Forward Transfer Admittance Note	y <sub>fs</sub>	Vds = -10.0 V, Id = -0.20 A	0.2	0.6		S
Drain to Source On-state Resistance Note	RDS(on)1	Vgs = -4.5 V, Id = -0.20 A		1.17	1.45	Ω
	RDS(on)2	$V_{GS} = -4.0 \text{ V}, \text{ Id} = -0.20 \text{ A}$		1.25	1.55	Ω
	RDS(on)3	Vgs = −2.5 V, Id = −0.15 A		2.25	2.98	Ω
Input Capacitance	Ciss	V <sub>DS</sub> = -10.0 V		29		pF
Output Capacitance	Coss	V <sub>G</sub> s = 0 V		15		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		3		pF
Turn-on Delay Time	td(on)	$V_{DD} = -10.0 \text{ V}, \text{ Id} = -0.20 \text{ A}$		23		ns
Rise Time	tr	Vgs = -4.0 V		39		ns
Turn-off Delay Time	td(off)	R <sub>G</sub> = 10 Ω		50		ns
Fall Time	tr			33		ns
Body Diode Forward Voltage	VF(S-D)	IF = 0.25 A, VGs = 0 V		0.88		V

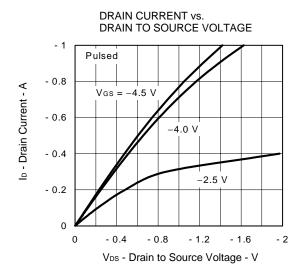
**Note** Pulsed: PW  $\leq$  350  $\mu$ s, Duty cycle  $\leq$  2%

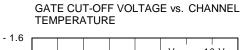
#### TEST CIRCUIT SWITCHING TIME

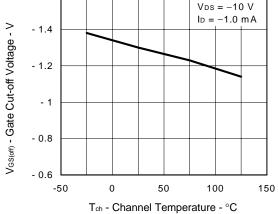


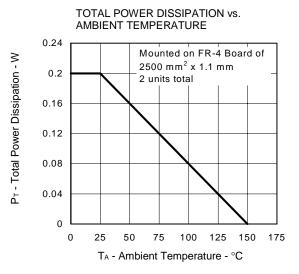
### **TYPICAL CHARACTERISTICS (TA = 25^{\circ}C)**



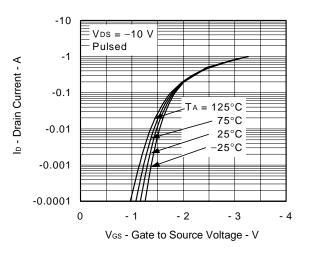




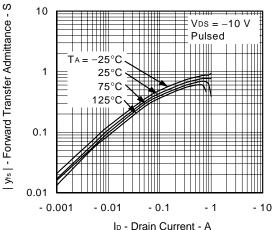




FORWARD TRANSFER CHARACTERISTICS



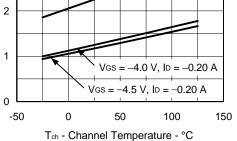
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



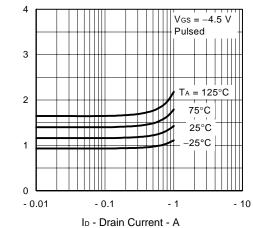


 $\mathsf{R}^{\mathsf{DS}(\mathsf{on})}$  - Drain to Source On-state Resistance -  $\Omega$ 

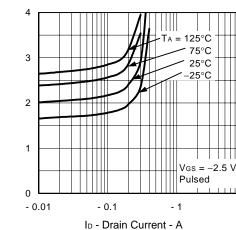
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



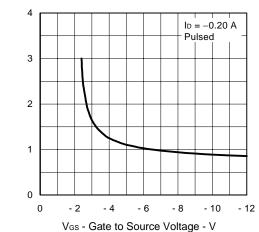
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

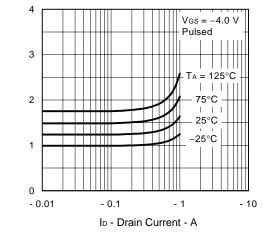


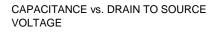
 $R_{DS(cn)}$  - Drain to Source On-state Resistance -  $\Omega$ 

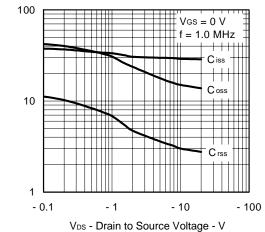
 $\mathsf{R}_{\mathsf{DS}(m)}$  - Drain to Source On-state Resistance -  $\Omega$ 

Ciss, Coss, Crss - Capacitance - pF

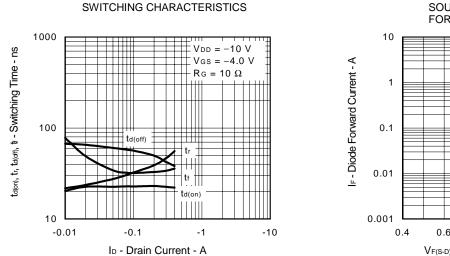
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



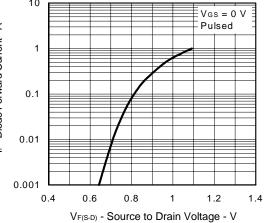




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#### SOURCE TO DRAIN DIODE FORWARD VOLTAGE



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